

Silicon NPN transistor in a TO-220F Plastic Package.

High f_T , complementary pair with .

General power and driver stage amplifier applications.



PIN1 Base PIN 2 Collector PIN 3 Emitter

/ h_{FE} Avicomp™

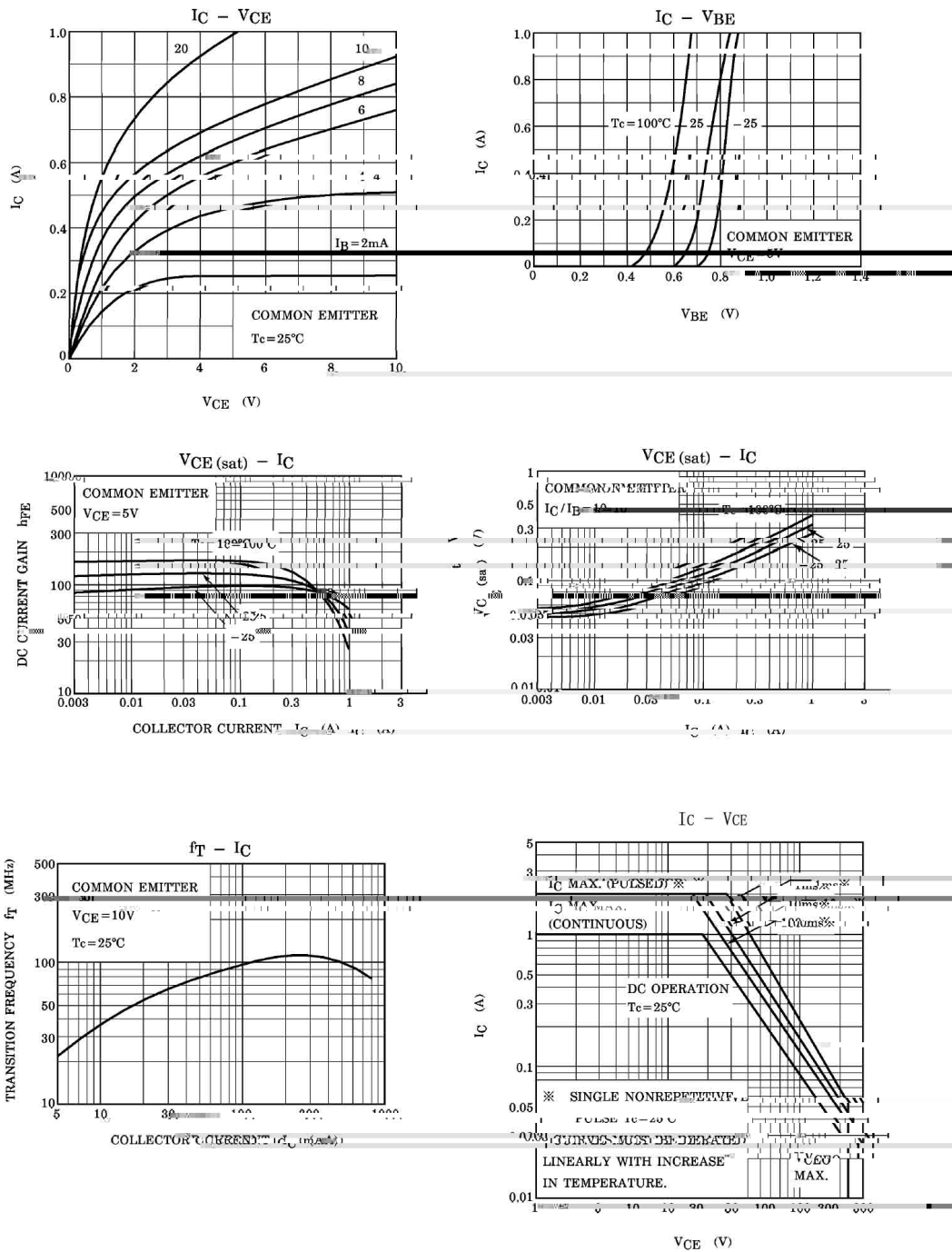
/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	230	V
Collector to Emitter Voltage	V_{CEO}	230	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	1.0	A
Base Current - Continuous	I_B	0.1	A
Collector Power Dissipation	P_C	2.0	W
	$P_{C(Tc=25)}$	20	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=10mA$ $I_B=0$	230			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=230V$ $I_E=0$			1.0	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=5.0V$ $I_C=0$			1.0	μA
DC Current Gain	h_{FE}	$V_{CE}=5.0V$ $I_C=100mA$	100		320	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=500mA$ $I_B=50mA$			1.5	V
Base to Emitter Voltage	V_{BE}	$V_{CE}=5.0V$ $I_C=500mA$			1.0	V
Transition Frequency	f_T	$V_{CE}=10V$ $I_C=100mA$		100		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V$ $I_E=0$ $f=1.0MHz$		20		pF

/ Electrical Characteristic Curve



/ Package Dimensions



3DA4793
Rev.F Mar.-2016

